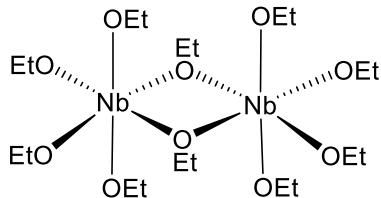


Catalog # 93-4104 Niobium(V) ethoxide (99.9+%-Nb)



## Thermal Behavior:

- Vapor pressure curve available in [7]
- TGA available in [7]

## Technical Notes:

1. Liquid alkoxide precursor for the growth of Nb oxide based thin films by ALD and CVD.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
$\text{Nb}_2\text{O}_5$	ALD	95-140 °C	7.5 Torr	$\text{D}_2\text{O}$	325 °C	[3]
$\text{Nb}_2\text{O}_5$	CVD	115 °C		air	300-450 °C	[1]
$\text{Nb}_2\text{O}_5$	PAALD	130 °C	7.5 Torr	-	180-245 °C	[12]
$\text{Nb}_{1-x}\text{Ta}_x\text{O}_5$	ALD	90-95 °C	7.5 Torr	$\text{H}_2\text{O}, \text{Ta}(\text{OEt})_5$	300-325 °C	[2, 4]
$\text{Nb}_{1-x}\text{Ta}_x\text{O}_5$	ALD	90 °C	7.5 Torr	$\text{H}_2\text{O}, \text{TaCl}_5$	300-325 °C	[2]
$\text{NbAl}_x\text{O}_y$	ALD	95 °C	7.5 Torr	$\text{H}_2\text{O}, \text{AlCl}_3$	300 °C	[4]
$\text{NbAl}_x\text{O}_y$	ALD		1.5 Torr	$\text{H}_2\text{O}, \text{Me}_3\text{Al}$	300 °C	[6]
$\text{NbTi}_x\text{O}_y$	ALD	90 °C	7.5 Torr	$\text{H}_2\text{O}, \text{Ti}(\text{OMe})_4$	215 °C	[5]
$\text{NbSi}_x\text{O}_y$	ALD	90-93 °C	7.5 Torr	$\text{O}_3, \text{Si}_2(\text{NHEt})_6$	300 °C	[15]
$\text{LiNbO}_3$	ALD	100 °C		$\text{H}_2\text{O}, \text{LiN}(\text{SiMe}_3)_2$	235 °C	[8]
$\text{LiNbO}_3$	ALD	155 °C		$\text{H}_2\text{O}, \text{LiO}^{\ddagger}\text{Bu}$	190 °C	[11]
$\text{NaNbO}_3$	ALD	68 °C	2 Torr	$\text{H}_2\text{O}, \text{NaO}^{\ddagger}\text{Bu}$	200-350 °C	[9]
$\text{KNbO}_3$	ALD	68 °C	2 Torr	$\text{H}_2\text{O}, \text{KO}^{\ddagger}\text{Bu}$	200-350 °C	[9]

RbNbO <sub>3</sub>	ALD	70 °C	2.1 Torr	H <sub>2</sub> O, RbO <sup>t</sup> Bu	250 °C	[10]
K <sub>x</sub> Na <sub>1-x</sub> NbO <sub>3</sub>	ALD	68 °C	0.8 Torr	H <sub>2</sub> O, NaO <sup>t</sup> Bu, KO <sup>t</sup> Bu	250 °C	[13]
KTa <sub>x</sub> Nb <sub>1-x</sub> O <sub>3</sub>	ALD	70 °C	2.1 Torr	H <sub>2</sub> O, KO <sup>t</sup> Bu, Ta(OEt) <sub>5</sub>	250 °C	[14]

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